

Day 1 (Monday, July 7)		Room Titane 2	
Session 1 – Remote and van der Waals epitaxy			
			Chair:
Time	Speaker	Title	
08:15 – 08:20	Bérangère Hyot CEA, Leti	Welcome	
08:20 – 08:30	Thomas Ernst CEA, Leti	Introduction and Welcome	
08:30 – 09:10	Ionut Radu SOITEC, France	Single-crystalline thin films à la carte: applications and technology opportunities	
09:10 – 09:30	Kyusang Lee Future Semiconductor Business, USA	From Laboratory to Industry: Remote Epitaxy for Scalable Semiconductor Membranes	
09:30 – 09:50	Hyunseok Kim University of Illinois Urbana-Champaign, USA	Is remote epitaxy really remote? – Unveiling the mode of epitaxy on 2D materials	
09:50 – 10:05	Coffee Break (15 min)		

Session 2 – Monolithic 3D integrations			
			Chair:
Time	Speaker	Title	
10:05 – 10:45 Plenary	Jeewan Kim MIT (Massachusetts Institute of Technology), USA	Seamless wafer-free monolithic 3D integration enabled by confined growth and remote epitaxy	
10:45 – 11:15 Keynote	Saptarshi Das Penn State University, USA	2D Materials for 3D Integration, Advanced Logic, and More	
11:15 – 11:45 Keynote	Qing Cao University of Illinois Urbana-Champaign, USA	Monolithic three-dimensional integration of complementary single-crystalline silicon transistors	
11:45 – 12:05	Jiho Shin TAMU (Texas A&M University), USA	Dissolvable, Flexible, and 3D-integrated electronics using freestanding membranes	
12:05 – 13:35		Lunch Break (90 min)	

Session 3&4 – Remote and van der Waals epitaxy			
			Chair:
Time	Speaker	Title	
13:35 – 14:15 Plenary	Chang-Beom Eom University of Wisconsin-Madison, USA	Twisted oxide membrane interface by local atomic registry design	
14:15 – 14:45 Keynote	Young Joon Hong SKKU (Sungkyunkwan University), South Korea	Nitride-based MOCVD remote epitaxy for high-performance device applications	
14:45 – 15:05	Hyun S. Kum Yonsei University, South Korea	Rapid low-temperature formation of graphene-coated SiC substrates for remote and vdW epitaxy	
15:05 – 15:35 Keynote	Jian Shi RPI (Rensselaer Polytechnic Institute), USA	Electrical and Optoelectronic Phenomena at van der Waals 2D–3D Phase-Transition Compound Interfaces	
15:35 – 16:05 Keynote	Abdallah Ougazzaden Yonsei University, South Korea	2D hBN in GaN Optoelectronics: Dual Roles in Epitaxial Engineering and Device Innovation.	
16:05 – 16:30	Coffee Break		

Panel Discussion - Meet the Editors		
Time	Panel	Topic
16:30 – 17:15	Karl Ziemelis (Nature, Chief Applied & Physical Sciences Editor) Mathew Parker (Nature Electronics) Olga Bubnova (Nature Sensors) Joern Ritterbush (Advanced Functional Materials, Chief editor)	Open discussion with panels, organizers, and attendees

Poster Session	
Time	
17:15 – 18:15	Poster Session
18:15 – 20:00	Wine and Cheese Tasting

Day 2 (Tuesday, July 8)		Room Titane 2	
Session 5 – Remote and van der Waals epitaxy			
			Chair:
Time	Speaker	Title	
09:10 – 09:30	Sungkyu kim Sejong University, South Korea	0	
09:30 – 09:50	Celesta Chang SNU (Seoul National University), South Korea	Visualizing freestanding membranes in 3D by electron ptychography	
09:50 – 10:10	Wei Kong Westlake University, USA	0	
10:10 – 10:30	Takuji Maekawa ROHM Co., Ltd., Japan	Fabrication of SiC remote epitaxial membranes for wafer cost reduction	
10:30 – 10:45	Coffee Break (15 min)		

Session 7 – Growth and Applications of membrane			
			Chair:
Time	Speaker	Title	
10:45 – 11:05	Tobias Henksmeier Paderborn University, Germany	Remote Epitaxy of III-V films on monolayer amorphous carbon covered substrates	
11:05 – 11:25	Jinkyoungh Yoo Los Alamos National Laboratory, USA	0	
11:25 – 11:45	Yoshitaka Taniyasu NTT Basic Research Laboratories, Japan	0	
11:45 – 12:05	Yuta Saito Tohoku University, Japan	Growth and Synthesis of layered tellurides for field effect transistor application	
12:05 – 12:25	Pavan Nukala IISc (Indian Institute of Science), India	Device quality epitaxial ferroelectric oxides obtained through various layer transfer techniques	
12:25 – 13:45	Lunch Break (80 min)		

Session 9 – Monolithic 3D integrations			
			Chair:
Time	Speaker	Title	
13:45 – 14:15	Didier Landru SOITEC	Membranes manufacturing with SOI & SmartCutTM technology	
14:15 – 14:45	Perrine Batude Leti	Status on 3D sequential integration with low temperature stacked Silicon devices	
14:45 – 15:05	Kyusang Lee UVA (University of Virginia), USA	CMOS + X towards edge intelligence	
15:05 – 15:25	Jianshi Tang Tsinghua University, Beijing, China	Monolithic 3D Integration with BEOL-Compatible Materials and Devices for Energy-Efficient Computing-in-Memory	
15:25 – 15:55	Sang-Hoon Bae Washington University in St. Louis, USA	Materials Innovation through 2D materials and 3D nanomembranes: From artificial heterostructures to M3D integration	
15:55 – 16:15	Coffee Break (20 min)		

Showroom visit	
16:15 – 18:15	

Gala Dinner	
18:15 – 22:30	Conference dinner at Château de la Commanderie (for Oral presenters, Panelists, and Organizers.) (There will be a shuttle bus from Minatec to Château de la Commanderie)

Day 2 (Tuesday, July 8)		Room Chrome 1	
Session 6 – Synthesis and Applications of 2D materials			
			Chair:
Time	Speaker	Title	
08:30 – 09:10 Plenary	Jiwoong Park University of Chicago, USA	More Magic with 2D Materials	
09:10 – 09:30	Ying-Hao Eddie Chu National Tsing Hua University, Taiwan	Van der Waals heteroepitaxy of Bi2O2X (X=S, Se, Te).	
09:30 – 09:50	Kibum Kang KAIST (Korea Advanced Institute of Science & Technology), South Korea	Towards Ultimate Nucleation-Control in 2D Film Growth	
09:50 – 10:10	Adrien Michon CNRS-CRHEA, France	Self-limited monolayer graphene growth on SiC with propane-hydrogen CVD	
10:10 – 10:30	Varun Harbola Max Planck Insitute, Germany	Heterointegration and interface design beyond epitaxy	
10:30 – 10:45	Coffee Break (15 min)		

Session 8 – Applications of free-standing membranes			
			Chair:
Time	Speaker	Title	
10:45 – 11:15	Nanshu Lu UT-Austin (University of Texas-Austin), USA	Graphene E-Tattoos	
11:15 – 11:45	Nini Pryds DTU (Technical Univeristy of Denmark), Denmark	Oxide Membranes: Fabrication, Transfer, and Stacking – Current Advances and Future Outlook	
11:45 – 12:05	Sean Li UNSW Sydney (University of New South Wales), Australia	Thickness-Dependent Mechanical and Physical Properties of Freestanding Single-Crystalline High-κ	
12:05 – 12:25	Minjoo Larry Lee University of Illinois Urbana-Champaign, USA	0	
12:25 – 12:45	Abderraouf Boucherif Université de Sherbrooke, Canada	Engineering Flexible Nanomembranes Using Porous Semiconductors and Graphene	
12:45 – 13:45	Lunch Break (60 min)		

Session 10 – Synthesis and Applications of 2D materials			
			Chair:
Time	Speaker	Title	
13:45 – 14:15	Deji Akinwande UT-Austin (University of Texas-Austin), USA	0	
14:15 – 14:45	Lain-Jong Li University of Hong Kong, Hong Kong	The Potential of Transition Metal Dichalcogenides for Low-Power Electronics: CFET Demonstration	
14:45 – 15:05	He Ding BIT (Beijing Institute of Technology), China	Ripple-free, high-performance DC voltage converter based on integrated	
15:05 – 15:25	Salim El Kazzi AIXTRON	Enabling Next-Gen 3D Integration via Wafer-Scale Epitaxy on 2D Materials	
15:25 – 15:45	Sanghoon Chae Nanyang Technological University (NTU), Singapore	Electrically Tunable Nonlinear Photonics using Ferroelectric 2D Materials Integration	
15:45 – 16:05	Coffee Break (20 min)		

Day 3 (Wednesday, July 9)		Room Titane 2	
Session 11 – Applications of free-standing membranes			
			Chair:
Time	Speaker	Title	
09:10 – 09:50 Plenary	Sheng Xu University of California San Diego, USA	Controlled epitaxial growth and fabrication of hybrid halide perovskite membranes	
09:50 – 10:20 Keynote	Dong-Seon Lee GIST (Gwangju Institute of Science and Technology), South Korea	0	
10:00 – 10:20	Yun Seog Lee SNU (Seoul National University), South Korea	0	
10:40 – 10:55 Coffee Break (15 min)			

Session 13 – Applications of free-standing membranes		
		Chair:
Time	Speaker	Title
10:55 – 11:15	MunHo Kim Nanyang Technological University (NTU), Singapore	Nanostructured Inorganic Wide Bandgap Semiconductors for Advanced Ultraviolet Photodetectors
11:15 – 11:35	Ning Li Penn State University, USA	0
11:35 – 11:55	Junwoo Son SNU (Seoul National University), South Korea	Single-crystalline rutile oxide nanomembranes: a versatile platform to overcome lattice mismatch
11:55 – 12:15	Yimo Han Rice University, USA	Strain and strain relaxation in van der Waals epitaxy revealed by advanced electron microscopy. (online)
12:15 – 13:45	Lunch Break (90 min)	

Day 3 (Wednesday, July 9)		Room Chrome 1	
Session 12 – Synthesis and Applications of 2D materials			
			Chair
Time	Speaker	Title	
09:10 – 09:40	Vincent Tung University of Tokyo, Japan	online?	
09:40 – 10:00	Yui Ogawa NTT Basic Research Laboratories, Japan	Investigation of the Growth Mechanism of Graphene in CVD Process via In-Situ Ultraviolet Optical Observation	
10:00 – 10:20	Matthieu Jamet CEA-Spintec, France	Large area epitaxial van der Waals heterostructures: new materials for tunable spintronic THz emission	
10:20 – 10:40	Haozhe Wang Duke University, USA	Foundation Model Agent for 2D Materials Characterization (online)	
10:40 – 10:55	Coffee Break (15 min)		

Session 14 – Applications of free-standing membranes			
			Chair
Time	Speaker	Title	
10:55 – 11:15	Nikhil Jain Xdisplay, USA	0	
11:15 – 11:35	Jens Martin Leibniz Institute, Germany	Fabrication pathways for freestanding oxide membranes and novel crystalline interfaces	
11:35 – 11:55	Matthew Lefevre Park Systems, France	Characterizing the electronic properties of graphene on silicon carbide via Atomic Force Microscopy"	

Closing Remark